

5 é / Descriptions

SOD-323 .> // x J ' ! - } 8 â 'ož

Silicon Diode in a SOD-323 Plastic Package.

□^a / Features

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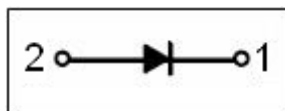
Fast switching diodes. HF Product.

Đ ÷ / Applications

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Small signal diode.

Ã W] Ô · / Equivalent Circuit



• Ů - æ / Pinning



PIN1:Cathode

PIN2:Anode

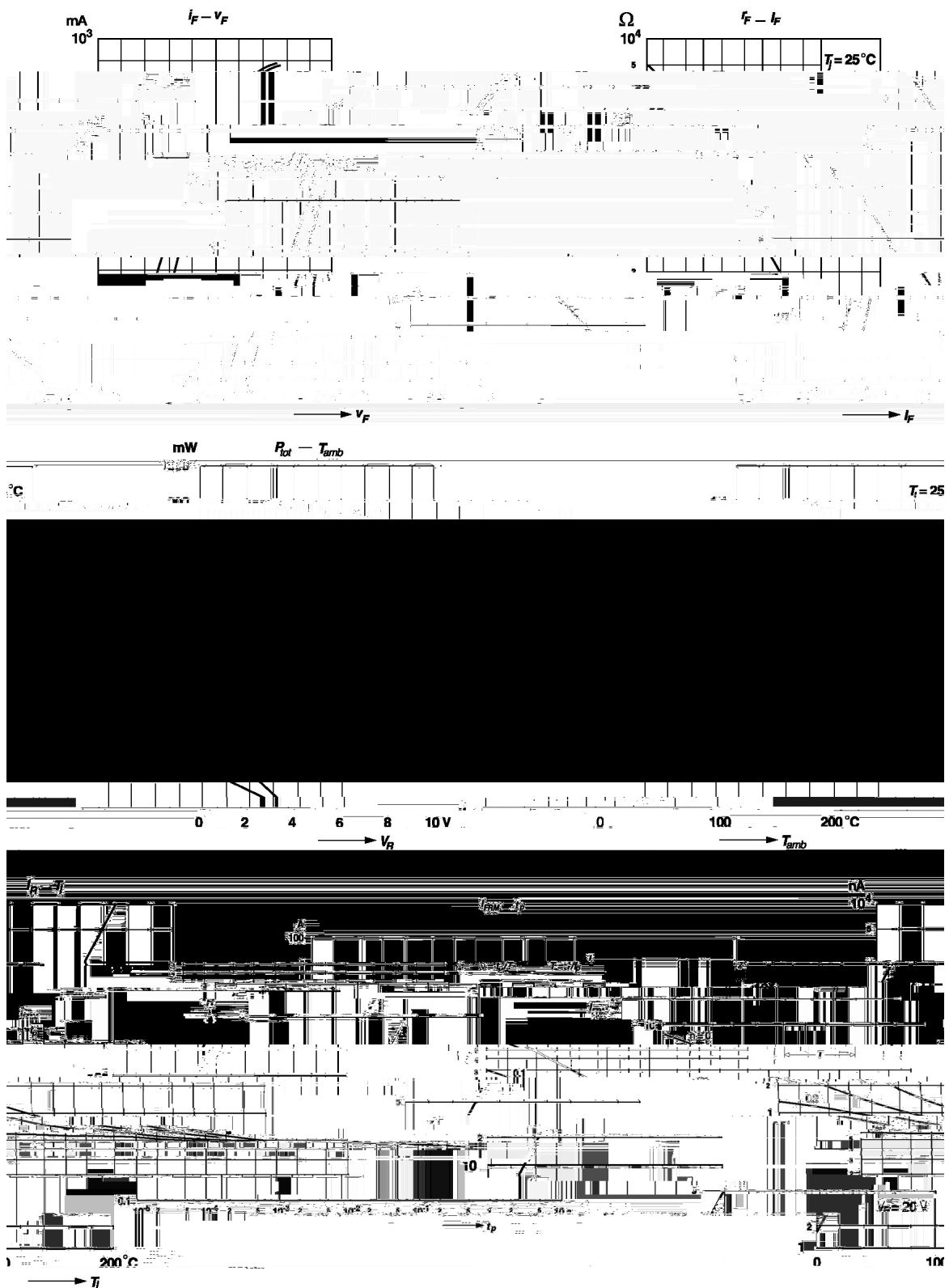
Z Ü B , M V / h_{FE} Classifications & Marking

Marking	HA2

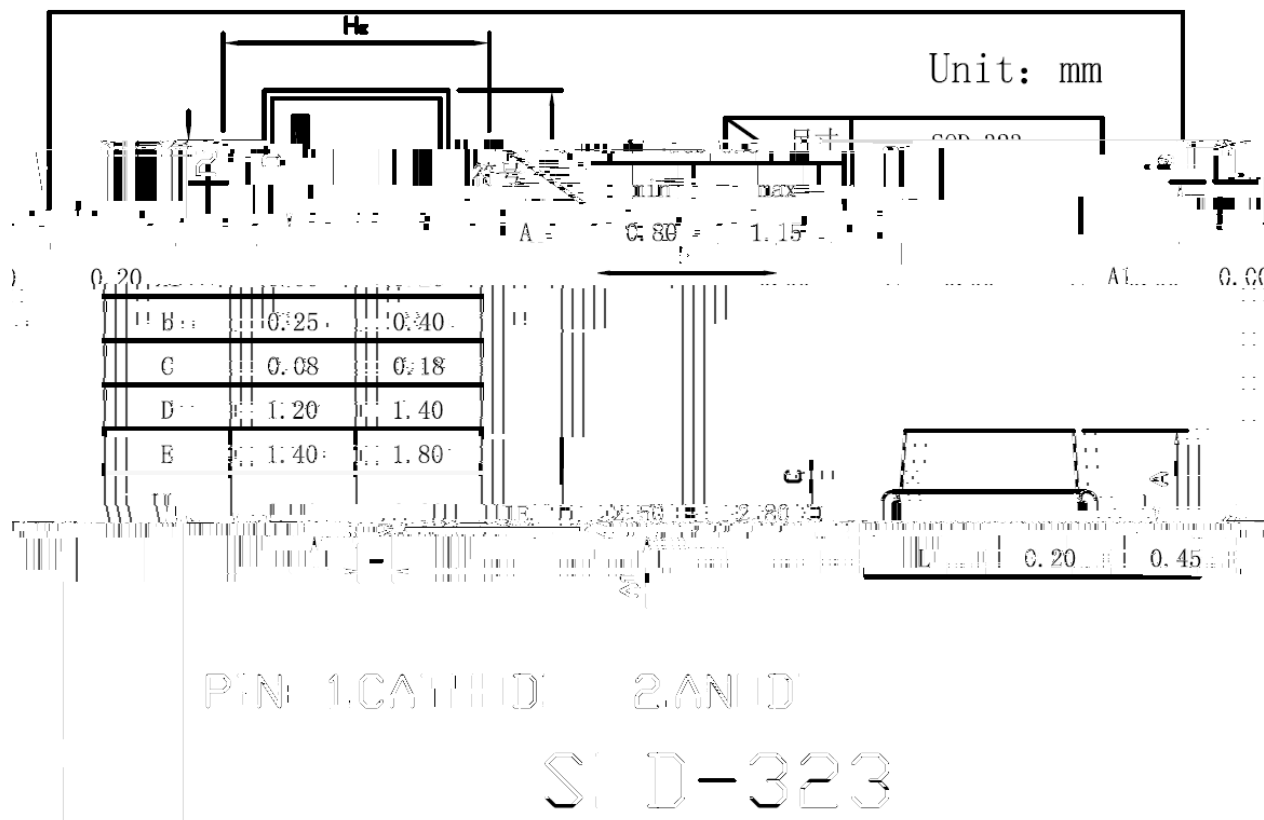
@ f Parameter	... Z Symbol	f > Rating	% y Unit
Reverse Voltage	V_R	75	V
Peak Reverse Voltage	V_{RM}	100	V
Average Rectified Output Current	I_O	150	mA
Forward Continuous Current	I_{FM}	300	mA
Non-Repetitive Peak Forward Surge Current	$I_{FSM} \Delta t=1.0 \text{ s}$	2.0	A
	$I_{FSM} \Delta t=1.0 \text{ s}$	1.0	A
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	
Thermal Resistance Junction to Ambient Air	R_{JA}	625	/W

@ f Parameter	... Z Symbol	y i Ú ^ Test Conditions	Â 4 > Min	Â ° > Typ	Â Ý > Max	% y Unit
Forward Voltage	V_F	$I_F=10\text{mA}$			1.0	V
Instantaneous Reverse Current	I_R	$V_R=20\text{V}$			25	nA
		$V_R=75\text{V}$			5	A
		$V_R=20\text{V} \quad T_j=150$			50	A
Capacitance	C_{tot}	$V_F=V_R=0\text{V}$			4	pF
Reverse Recovery Time	t_{rr}	$I_F=10\text{mA} \quad V_R=6.0\text{V}$ $I_R=1\text{mA} \quad R_L=100$			4	ns
Voltage Rise when Switching On tested	V_{fr}	$t_p=0.1 \text{ s} \quad f_p=5\text{to}100\text{kHz}$ Time<30ns			2.5	V
Total Capacitance	C_T	$V_R=0 \quad f=1.0\text{MHz}$			2.0	pF

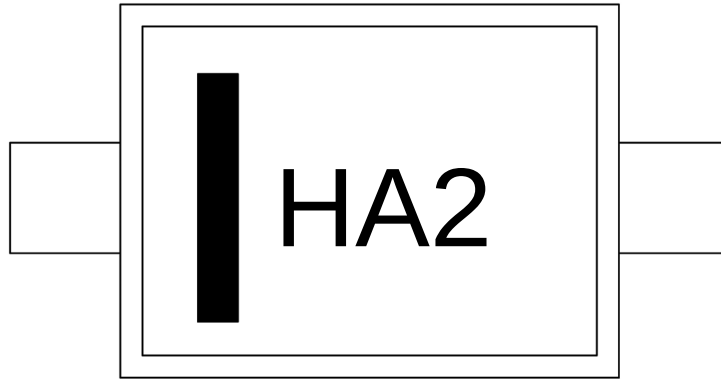
Electrical Characteristic Curve



Ø □ =) ¢ / Package Dimensions



Marking Instructions



Marking

Marking [W A

Marking ° Z W A

Note:

H: Company Code.

A2: Product Type.

